

**AMENDMENTS TO THE SPECIFICATION**

Please amend paragraph [0001] as follows:

[0001] The present invention relates to resistive memory devices and, more particularly, to read/sense circuitry for ~~programmable contact random access memory (PCRAM)~~ resistive memory devices.

Please amend paragraph [0002] as follows:

[0002] Integrated circuit designers have always sought the ideal semiconductor memory – a device that is randomly accessible, can be written and read very quickly, is non-volatile, but indefinitely alterable, and consumes little power. Resistive memories, including programmable ~~Programmable~~ contact random access memory (PCRAM) technology has been increasingly viewed as offering all these advantages.

Please amend paragraph [0036] as follows:

[0036] While embodiments of the invention have been described in the illustrations above, it should be understood that these are exemplary of the invention and are not to be considered as limiting. While the present invention has been described in terms of PCRAM, it is not limited thereto but is applicable to, for example, magnetic resistive random access memory (MRAM) PCRAM and other resistive memory circuits in which signals are sensed at different levels. Additions, deletions, substitutions, and other modifications can be made without departing from the spirit or scope of the present invention. Accordingly, the invention is not to be considered as

limited by the foregoing description but is only limited by the scope of the appended claims.

Please amend paragraph [0020] as follows:

[0020] In response to signals 130 and 135, switching circuit 110 provides two signals to comparison circuit 115 via two signal lines 122. At any point in time at which a comparison is made between the ~~signal~~ signals, on lines 125, one signal line 122 is at the supply voltage  $V_{cc}$  and the other is at a voltage that depends on resistance element 30. The signal through resistance element 30 alternates polarity during a read operation.